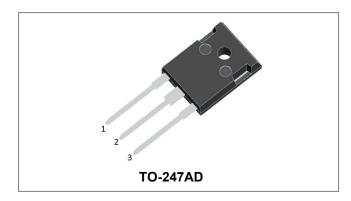






MBR6040WT/MBR6045WT SCHOTTKY RECTIFIER



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- · High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	40	MBR6040WT	
Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RWM} \ V_{R} \end{array}$		45	MBR6045WT	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=135°C, rectangular wave form	30(Per Leg) 60(Per Device)		Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	432		А
Repetitive Avalanche Current(Per Leg)	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T _J max.V _A =1.5×V _R typical	6		А
Non-Repetitive Avalanche Energy(Per Leg)	E _{AS}	T _J =25°C,I _{AS} =4A,L=3.4mH	27		mJ

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 30A, Pulse, T _J = 25℃	0.54	0.65	V
(Per Leg)*	V _{F2}	@ 30A, Pulse, T _J = 125℃	0.50	0.55	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R ,T _J = 25℃	0.2	1.0	mA
	I _{R2}	@V _R = rated V _R ,T _J = 125℃	70	150	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25^{\circ}C,$ $f_{SIG} = 1MHz$	1595	1650	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^*}$ Pulse width < 300 μ s, duty cycle < 2%

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com
 sales@ smc-diodes.com



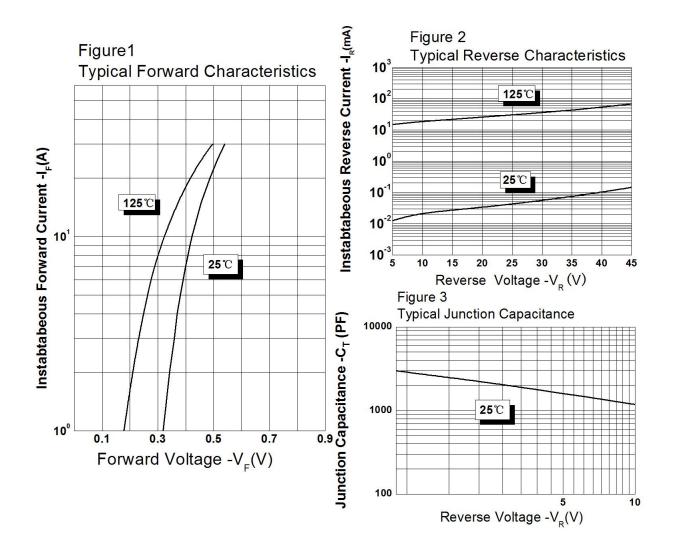




Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to	R _θ JC	DC operation	1.0(per leg)	°C/W
Case			0.5(per package)	
Typical Thermal Resistance, Case to	R₀cs	Mounting surface, smooth and	0.24	°C/W
Heat Sink		greased		
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Ratings and Characteristics Curves



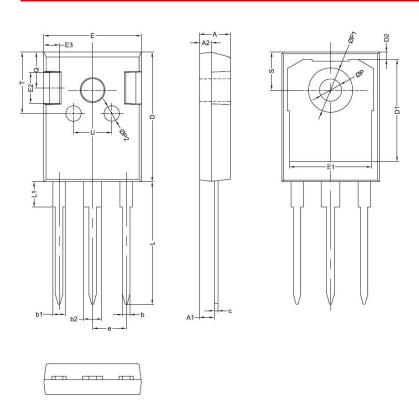
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Mechanical Dimensions TO-247AD



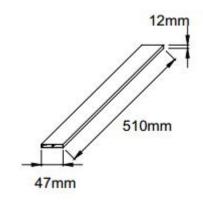
CVMDOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
Α	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
		1.20			
D2 E	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
		5.44			
<u>е</u> L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
Q S	6.05	6.15	6.25		
T		10.00			
U		6.20			

Ordering Information:

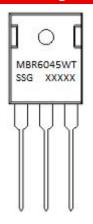
Device	Package	Shipping	
SDUR6040WT/SDUR6045WT	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type 60 = Forward Current (60A) 40/45 = Reverse Voltage (40V/45V) WT = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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